ISOLATION TRENCHES FOR MEMORY DEVICES

ABSTRACT

A first dielectric plug is disposed in a portion of a trench that extends into a substrate of an integrated device so that an upper surface of the first dielectric plug is located below an upper surface of the substrate. The first dielectric plug has a layer of a first dielectric material in contact with a layer of a second dielectric material interposed between the substrate and the layer of the first dielectric material. A second dielectric plug of a third dielectric material is disposed in the trench on the upper surface of the first dielectric plug.

Figure 2H